Fig 2.2 Lithographic Step of Positive and negative photoresist
Fig 4. 3 (a) Standing wave observed in a structure developed without post-exposure treatment (b) Effect of post exposure treatment (115°C, 45 sec) [23]
Fig 6.1 Principle of Gel Permeation Chromatography
Fig 6.2 Principle of the scanning electron microscope (BSE = backscattered electrons, SE = secondary electrons, SC = specimen current, EBIC= electron-beam-induced current, X= x-rays, CRT= Cathode-ray tube [35].
Fig 12.9 Optical micrograph of resist 234

Fig 12.10 Optical micrograph of resist 244
Fig 12.11 Optical micrograph of resist TNQ

Fig 12.12 Optical micrograph of resist 14NAC5
Fig 12.13 A general view of image of resist 234 with SEM
Fig 12.14 A general view of image of resist 244 with SEM
Fig 12.15 SEM pictures(high magnification) of resist 234
Fig 12.16 SEM picture (high magnification) of resist 244
Fig 12.17 SEM picture (low magnification) of 14NAC5

Fig 12.18 SEM picture (low magnification) of TNQ
Fig 12.19 SEM pictures (high magnification) of photoresist 14NAC5
Fig 12.20 SEM pictures (high magnification) of photoresist TNQ